Approved for use through 07/31/2006. OMB 0651-0031 and Trademark Office; U.S. DEPARTMENT OF COMMER

Under the Paperwork Reduction Act of 1995.	, no persoi	ns are required t	to respond to a collection of in	formation unless it displays a valid OMB control nu
			Application Number	10/514,429
TRANSMITTAL FORM			Filing Date	July 12, 2005
			First Named Inventor	Robert DWILINSKI
(to be used for all correspondence at	fter initial fi	ilina)	Art Unit	2879
(to be used for all correspondence after milital lilling)			Examiner Name	Not Yet Assigned
Total Number of Pages in This Subm	ission	4	Attorney Docket Number	204552033800
E	NCLO	SURES (	Check all that appl	/y)
Fee Transmittal Form		Drawing(s)		After Allowance Communication to TC
Fee Attached		Licensing-related Papers		Appeal Communication to Board of Appeals and Interferences
Amendment/Reply		Petition		Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)
After Final	1 1 1	Petition to Co Provisional A		Proprietary Information
Affidavits/declaration(s)			rney, Revocation	Status Letter

Affidavits/declaration(s)		Power of Attorney, Revocation Change of Correspondence Address		Status Letter		
Extension of Time Request		Terminal Disclaimer		X Other Enclosure(s) (please Identify below):		
Express Abandonment Request		Request for Refund		1. 2.	Form PTO/SB/08a/b (1 page) Copies of IDS Citations (6 refs)	
X Information Disclosure Statement		CD, Number of CD(s)		Return Receipt Postcard		
Certified Co	opy of Priority s)	Landscape Tab	e on CD			
Reply to Missing Parts/ Incomplete Application		Remarks				
Reply 37 CF	y to Missing Parts under FR 1.52 or 1.53					
	SIGNATI	URE OF APPLICANT, AT	TORNEY OR	ΔGF		
irm Name	MORRISON & FOE				···	
Signature	l arin					
Printed name	Raj S. Davé	. '				
Date	December 19, 2005		Reg. No.	42,4	465	

EFS-Web Receipt date: 12/19/2005.

10514429 - GAU: 2881

PATENT Docket No. 204552033800



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Robert DWILINSKI et al.

Serial No.: 10/514,429

Filing Date: July 12, 2005

For: PHOSPHOR SINGLE CRYSTAL

SUBSTRATE AND METHOD FOR PREPARING THE SAME, AND

NITRIDE SEMICONDUCTOR DEVICE

USING THE SAME

Examiner: Not Yet Assigned

Group Art Unit: 2879

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97 & 1.98

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

## Dear Sir:

Pursuant to 37 C.F.R. § 1.97 and § 1.98, Applicants submit for consideration in the above-identified application the documents listed on the attached Form PTO/SB/08a/b. Copies of the non-patent literature are also submitted herewith. The Examiner is requested to make these documents of record.

Six of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 13-18) were cited in a Notification mailed September 27, 2005, directed to a related foreign application JP2003-503864, and have not been previously cited; one of the documents listed on the attached Form PTO/SB/08a/b (Cite No. 12) was cited in an Office Action mailed October 19, 2005, directed to a related application US 10/147,319, and has not been previously cited; two of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 1 and 2) were cited in an Office Action mailed October 4, 2005, directed to a related application US 10/479,858, and have not been previously cited; and nine of the documents listed on the attached Form PTO/SB/08a/b (Cite Nos. 3-11) were cited in an Office Action mailed November 4, 2005, directed to a related

va-146119 /Michael Logie/ 05/29/2008 ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /M:L./

Atty. Docket No. 204552033800

10514429 - GAU: 2881

'U.S. Serial No. 10/514,429

application US 10/493,747, and have not been previously cited. A certification under 37 C.F.R. § 1.97(e)(1) follows:

I hereby certify that each item of information was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

This Information Disclosure Statement is submitted within three months of the application filing date or before mailing of a first Office Action on the merits; accordingly, no fee or separate requirements are required.

Applicants would appreciate the Examiner initialing and returning the Form PTO/SB/08a/b, indicating that the information has been considered and made of record herein.

The information contained in this Supplemental Information Disclosure Statement under 37 C.F.R. § 1.97 and § 1.98 is not to be construed as a representation that: (i) a complete search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the above information constitutes prior art to the subject invention.

In the unlikely event that the transmittal form is separated from this document and the Patent Office determines that an extension and/or other relief (such as payment of a fee under 37 C.F.R. § 1.17 (p)) is required, Applicants petitions for any required relief including extensions of time and authorize the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952** referencing 204552033800.

Dated: December 19, 2005

Respectfully submitted.

Registration No.: 42,465

Morrison & Foerster LLP

1650 Tysons Boulevard, Suite 300

McLean, Virginia 22102 Telephone: 703.760.7700

Facsimile: 703.760.7777

/Michael Logie/

ALTERNATIVE TO PTO/SB/08a/b (07-05)

FS-Web Receipt date: 12/19/2005.

Substitute for form 1449/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

1 Sheet 1

	Complete if Known
Application Number	10/514,429
Filing Date	July 12, 2005
First Named Inventor	Robert DWILINSKI
Art Unit	2879
Examiner Name	Not Yet Assigned
Attorney Docket Number	204552033800

U.S. PATENT DOCUMENTS						
Examiner		Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where
Initials		No.1	Number-Kind Code <sup>2</sup> (if known)	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
8 /	/M.L	.1/.	5,096,860-A	03-17-1992	NADKARNI	
000		2.	5,589,153-A	12-31-1996	GARCES	
		3.	6,252,261-B1	06-26-2001	USUI	
		4.	6,468,882-B2	10-22-2002	мотокі	
		5.	6,509,651-B1	01-21-2003	MATSUBARA	
		6.	6,720,586-B1	04-13-2004	KIDOGUCHI	
		7.	2002/0014631-A1	02-07-2002	IWATA	
		8.	2002/0031153-A1	03-14-2002	NIWA	
		9.	2002/0047113-A1	04-25-2002	OHNO	
		10.	2002/0063258-A1	05-30-2002	MOTOKI	
	'	11.	2002/0078881-A1	06-27-2002	CUOMO	
<b>  W</b>	/M_I	1/2.	2004/0139912-A1	07-22-2004	TOMASZ DWILINSKI	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>6</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>	

<sup>\*</sup>EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at <a href="www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Cite Initials No.1		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>		
Akasaki, I. et al. (1991). "Growth and Properties of Single Crystalline GaN Films by Hydride Vapor Phase Epitaxy," Crystal Properties and Preparation 32-34:154-157.					
0000000	14.	Chu, T. L. et al. (1974). "Crystal Growth and Characterization of Gallium Nitride," <i>J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY</i> 121-1:159-162.			
	15.	Kaschner, A. et al. (1999). "Influence of Doping on the Lattice Dynamics of Gallium Nitride," MRS Internet J. Nitride Semicond. Res. 4S1, G3.57.			
9922220000	16.	Kim, S. T. et al. (1998). "Preparation and Properties of Free-standing HVPE Grown GaN Substrates," <i>Journal of Crystal Growth</i> 194:37-42.			
4	17.	Kuroda, Naotaka et al. (1998). "Precise Control of Pn-junction Profiles for GaN-based LD structures Using GaN Substrates with Low Dislocation Densities," <i>Journal of Crystal Growth</i> 189/190:551-555.			
<b>V</b> /M	18. L./	Motoki, Kensaku et al. (2001). "Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a Starting Substrate," <i>J. Appl. Phys.</i> 40:L140-L143.			

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	/Michael Logie/	Date Considered	05/29/2008